

3. (Amended) A semiconductor integrated circuit device according to claim 1, further comprising a power supply terminal to which an external power supply voltage is applied and a ground terminal, wherein a transistor [whose] having a current path [is] connected between the power supply terminal and the ground terminal [being] is one of the transistors other than the transistor having the thinnest gate insulation film.

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4. (Amended) A semiconductor integrated circuit device according to claim 1, further comprising an interface circuit connected to the input/output terminal, wherein a transistor [which constitutes part of] included in the interface circuit and [is] connected directly to the input/output terminal [being] is one of the transistors other than the transistor having the thinnest gate insulation film.

5. (Amended) A semiconductor integrated circuit device according to claim 4, wherein a transistor [which constitutes part of] included in the interface circuit and [is] connected directly to a power supply terminal is one of the transistors other than the transistor having the thinnest gate insulation film.

Claim 6, *AB* lines 2-3, delete "which constitutes part of" and insert --included in--.

14. (Amended) A semiconductor integrated circuit device according to claim 13, wherein a transistor [which constitutes part of] included in the level shifter and [is included in] a device directly receiving the lower potential level signal is the transistor having the thinnest gate insulation film.